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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/630,736	07/31/2003	Shinji Imai	Q76736	1390	
23373	7590 10/13/2004		EXAMINER		
SUGHRUE MION, PLLC 2100 PENNSYLVANIA AVENUE, N.W. SUITE 800			HANNAHER, CONSTANTINE		
			ART UNIT	PAPER NUMBER	
WASHINGTO	ON, DC 20037		2878	2878	
			DATE MAIL ED: 10/12/200	DATE MAILED: 10/13/2004	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)	
06: 4-4: 0	10/630,736	IMAI, SHINJI	
Office Action Summary	Examiner	Art Unit	
	Constantine Hannaher	2878	· · · · · · · · · · · · · · · · · · ·
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence ad	dress
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply - If NO period for reply is specified above, the maximum statutory period was Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	6(a). In no event, however, may a reply be time within the statutory minimum of thirty (30) days ill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONEI	nely filed s will be considered timely the mailing date of this co O (35 U.S.C. § 133).	
Status			
<ol> <li>Responsive to communication(s) filed on 14 Set</li> <li>This action is FINAL.</li> <li>Since this application is in condition for allowant closed in accordance with the practice under Extended</li> </ol>	action is non-final. ice except for formal matters, pro		merits is
Disposition of Claims			
4) ☐ Claim(s) 1-17 is/are pending in the application. 4a) Of the above claim(s) is/are withdraw 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 1-17 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or			
Application Papers			
9) The specification is objected to by the Examiner 10) The drawing(s) filed on is/are: a) access Applicant may not request that any objection to the or Replacement drawing sheet(s) including the correction 11) The oath or declaration is objected to by the Ex	epted or b) objected to by the Edrawing(s) be held in abeyance. See on is required if the drawing(s) is obj	e 37 CFR 1.85(a). ected to. See 37 CF	• •
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of:  1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the prior application from the International Bureau * See the attached detailed Office action for a list of	s have been received. s have been received in Applicati ity documents have been receive (PCT Rule 17.2(a)).	on No ed in this National	Stage
Attachment(s)  1) Notice of References Cited (PTO-892)  2) Notice of Draftsperson's Patent Drawing Review (PTO-948)  3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 20040914.	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:	ate	)-152)

Application/Control Number: 10/630,736

Art Unit: 2878

## **DETAILED ACTION**

## Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

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2. Claims 1-11 are rejected under 35 U.S.C. 103(a) as being unpatentable over Imai (EP0898421A2) in view of Fallone et al. (US005686733A) and Brauers et al. (US005729021A).

With respect to independent claim 1, Imai discloses an image recording medium having the six recited layers (since first electrode layer 5 comprises a glass plate which serves as support and is permeable to the reading electromagnetic wave, column 17, lines 30-33, and since the combination of recording photoconductive layer 2 and charge transport layer 3 serves as a charge accumulating portion, Fig. 3D). At least one of the photoconductive layers 2, 4 is formed of a material containing amorphous selenium as a major component, column 17, line 35, and column 18, line 6. Imai does not identify any doping. Fallone et al. discloses that an image recording medium with a photoreceptor layer of amorphous selenium is preferably doped with arsenic and chlorine (column 8, lines 64-65). Brauers et al. discloses that arsenic doping counteracts recrystallization of a layer of amorphous selenium in an image sensor (column 6, lines 35-36). Accordingly, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the image recording medium of Imai to dope the amorphous selenium layers therein as suggested by Fallone et al. especially in view of the advantageous counteraction of recrystallization identified by Brauers et al. for such doping.

With respect to dependent claim 2, the doping suggested by Brauers et al. for counteracting recrystallization is the recited element.

With respect to dependent claim 3, Fallone et al. makes explicit that the level of doping with arsenic is a choice within the ordinary skill in the art (column 8, line 67 to column 9, line 1). Brauers et al. discloses a range of doping with arsenic (column 6, lines 35-36) that encompasses the claimed range with sufficient specificity to establish obviousness. Accordingly, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the image recording medium of Imai to dope the amorphous selenium layers therein as suggested by Fallone et al. in an amount within the range identified by Brauers et al. for such doping in view of the effective performance in counteracting recrystallization.

With respect to dependent claim 4, as already established, Fallone *et al.* identifies doping a layer of amorphous selenium in an image recording medium with chlorine as routine and preferable (column 8, lines 64-65). Accordingly, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the image recording medium of Imai to dope the amorphous selenium layers therein as suggested by Fallone *et al.* with chlorine.

With respect to dependent claim 5, Fallone *et al.* makes explicit that the level of doping with chlorine is a choice within the ordinary skill in the art (column 8, line 67 to column 9, line 1).

With respect to dependent claims 6 and 7, the thickness of the recording photoconductive layer 2 in the image recording medium of Imai is in a range (see claim 3) which encompasses the recited ranges with sufficient specificity to establish obviousness.

With respect to independent claim 8, Imai discloses an image recording medium having the six recited layers (since first electrode layer 5 comprises a glass plate which serves as support and is permeable to the reading electromagnetic wave, column 17, lines 30-33, also note "charge transport

layer" 3). The charge transfer layer 3 is formed of a material containing amorphous selenium as a major component, column 17, lines 45-51 doped with chlorine. Fallone *et al.* discloses that an image recording medium with a photoreceptor layer of amorphous selenium is preferably doped with arsenic and with chlorine (column 8, lines 64-65). Brauers *et al.* discloses that arsenic doping counteracts recrystallization of a layer of amorphous selenium in an image sensor (column 6, lines 35-36). Accordingly, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the image recording medium of Imai to dope the amorphous selenium charge transfer layer therein as suggested by Fallone *et al.* especially in view of the advantageous counteraction of recrystallization identified by Brauers *et al.* for such doping.

With respect to dependent claim 9, see the explanation of the rejections against claims 2 through 5 above.

With respect to dependent claims 10 and 11, see the explanation of the rejection against claims 6 and 7 above.

3. Claims 12-17 are rejected under 35 U.S.C. 103(a) as being unpatentable over Imai (EP0898421A2) in view of Fallone et al. (US005686733A) and Brauers et al. (US005729021A) and Urabe (US004990420A).

With respect to independent claim 12, the image recording medium recited is made obvious by the combination of Imai, Fallone *et al.*, and Brauers *et al.*, see the explanation of the rejection against claims 1 through 7, notwithstanding the lack of requirement for amorphous selenium particularly. Urabe discloses that "resistance heating deposition" (column 5, lines 6-7) is a known method of forming a recording photoreceptor layer of an alloy material containing therein selenium as a major component, even one doped with arsenic in the claimed range and one doped with chlorine in the claimed range (column 5, lines 63-65). In view of the disclosed suitability of the

resistance heating deposition suggested by Urabe to form a layer as required by the combination of Imai, Fallone *et al.*, and Brauers *et al.*, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify any method of manufacturing disclosed by these references to specify the use of resistance heating deposition, especially since Imai does not identify any particular method of manufacturing.

With respect to dependent claims 13 and 14, see the explanation of the rejection against claims 6 and 7 above.

With respect to independent claim 15, the image recording medium recited is made obvious by the combination of Imai, Fallone et al., and Brauers et al., see the explanation of the rejection against claims 8 and 9, notwithstanding the lack of requirement for amorphous selenium particularly. Urabe discloses that "resistance heating deposition" (column 5, lines 6-7) is a known method of forming a recording photoreceptor layer of an alloy material containing therein selenium as a major component, even one doped with arsenic in the claimed range and one doped with chlorine in the claimed range (column 5, lines 63-65). In view of the disclosed suitability of the resistance heating deposition suggested by Urabe to form a layer as required by the combination of Imai, Fallone et al., and Brauers et al., it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify any method of manufacturing disclosed by these references to specify the use of resistance heating deposition, especially since Imai does not identify any particular method of manufacturing.

With respect to dependent claims 16 and 17, see the explanation of the rejection against claims 10 and 11 above.

## Response to Submission(s)

4. The amendment filed September 14, 2004 has been entered.

5. Applicant's arguments filed September 14, 2004 have been fully considered but they are not persuasive.

The denial that no reference or combination teaches that "the recording photoconductive layer is formed of a material containing a-Se as a major component and doped with a material for suppressing bulk crystallization of a-Se" is not persuasive when, as here, the Examiner has shown the recording photoconductive layer and its formation with a-Se in Imai, the exact dopant materials in Fallone *et al.*, and the exact dopant material and reason for doping a-Se in Brauers *et al.* 

For at least the reasons explained above, Applicant is not entitled to a favorable determination of patentability in view of the arguments submitted September 14, 2004.

## Conclusion

6. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Constantine Hannaher whose telephone number is (571) 272-2437. The examiner can normally be reached on Monday-Friday with flexible hours.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David P. Porta can be reached on (571) 272-2444. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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